

wherein the semiconductor laser chip is covered with the resin forming a molded lens and wherein the laser light is emitted through said molded lens.

2. (Amended) A semiconductor laser device according to claim 1, wherein the semiconductor laser chip does not directly contact the resin.

3. (Amended) A semiconductor laser device according to claim 1 further includes a light diffusion plate provided between the semiconductor laser chip and the molded lens.

4. (Amended) A semiconductor laser device including a semiconductor laser chip covered with resin, having a light diffusion capability and forming a molded lens, wherein the semiconductor laser chip includes a plurality of light emitting portions.

5. (Amended) A semiconductor laser device including a semiconductor laser chip covered with resin, having a light diffusion capability and forming a molded lens, wherein the semiconductor laser chip includes at least one light emitting portion having a width of about 7 μm or more.

6. (Amended) A semiconductor laser device including a semiconductor laser chip covered with resin, having a light diffusion capability and forming a molded lens further includes at least one additional semiconductor laser chip.

7. (Amended) A semiconductor laser device according to claim 4, wherein the spot size and radiation angle of an emitted light beam can be controlled by adjusting the intervals between each light emitting portion of the semiconductor laser chip including the plurality of light emitting portions, and the size, material, and shape of the molded lens.

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8. (Amended) A semiconductor laser device according to claim 5, wherein the spot size and radiation angle of an emitted light beam can be controlled by adjusting the width of the light emitting portion of the semiconductor laser chip including the light emitting portion having a width of about 7 μm or more, and the size, material, and dimension of the molded lens.

9. (Amended) A semiconductor laser device according to claim 6, wherein the spot size and radiation angle of an emitted light beam can be controlled by adjusting the intervals, between the semiconductor laser chips, and the size, material, and dimension of the molded lens.

10. (Amended) A semiconductor laser device according to claim 1, wherein materials having different refractive indexes are mixed into the molded lens.
